	Application No.	Applicant(s)	
Notice of Allowability	10/740 500	EJIRI, KAZUAKI	(m)
	10/749,599 Examiner	Art Unit	
	Las Cohim	2010	
	Lee, Calvin	2818	
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.31	S (OR REMAINS) CLOSED in this ap i) or other appropriate communication RIGHTS. This application is subject t	plication. If not includent will be mailed in due	ed course. <b>THIS</b>
1. X This communication is responsive to <u>Telephone Interview dated September 6, 2005</u> .			
2. The allowed claim(s) is/are 1,4-13 and 17.			
3. $\square$ The drawings filed on $\underline{12/31/03}$ are accepted by the Exam	niner.		
<ul> <li>4.  Acknowledgment is made of a claim for foreign priority of a)  All b)  Some* c)  None of the:</li> <li>1.  Certified copies of the priority documents have</li> <li>2.  Certified copies of the priority documents have</li> <li>3.  Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)).</li> </ul>	re been received. re been received in Application No	<del></del>	tion from the
* Certified copies not received:			
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDON! THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		complying with the red	quirements
5. A SUBSTITUTE OATH OR DECLARATION must be subminformal PATENT APPLICATION (PTO-152) which give			IOTICE OF
6. CORRECTED DRAWINGS ( as "replacement sheets") mu	ıst be submitted.		
(a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review ( PTO-948) attached			
1)  hereto or 2)  to Paper No./Mail Date			
(b) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date			
Identifying indicia such as the application number (see 37 CFR each sheet. Replacement sheet(s) should be labeled as such in			back) of
<ol> <li>DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT</li> </ol>			Note the
Attachment(s)	F □ Nation of Informal F	Potent Application (PT)	O 152)
1. Notice of References Cited (PTO-892)	<ol> <li>5. ☐ Notice of Informal F</li> <li>6. ☒ Interview Summary</li> </ol>		J-102)
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	Paper No./Mail Da	te <u>hereto</u> .	
<ol> <li>Information Disclosure Statements (PTO-1449 or PTO/SB/Paper No./Mail Date</li></ol>	7. ⊠ Examiner's Amendi 8. ⊠ Examiner's Stateme		nwance
of Biological Material	9. Other	Sint of Moadonia for Alle	
Devid Nelms			
Supervisory Patent Examiner			
Technology Center 2800			

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## **OFFICE ACTION**

## Examiner's Amendment

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. IN THE CLAIMS: Canceled claims 2-3;

Claim 1, line 6, after "abrasive slurry" inserted --, wherein said low-k material insulating layer is formed as a SiCOH layer or as a methyl silsesquioxane layer--;

Clain 1, line 9, after "polishing pad" insert --washing said semiconductor wafer, which is drenched with said aqueous abrasive slurry, with an aqueous washing solution; and rinsing the washed semiconductor wafer--;

Claim 10, line 2, after "further comprising" deleted --washing said semiconductor wafer, which is drenched with said aqueous abrasive slurry, with an aqueous washing solution; and--

2. Authorization for this examiner's amendment was given in a telephone interview with Donald W. Muirhead on September 6, 2005

## Allowable Subject Matter

3. Claims 1, 4-13, and 17 are allowed. Following is the examiner's reason for allowance:

The closest art, US 6,617,717 to Sachan et al, does not disclose, inter alia, a CMP method of a low-k material for making the low-k material being hydrophilic in nature, wherein the low-k material insulating layer is formed as a SiCOH layer or as a methyl silsesquioxane layer. Furthermore, Sachan et al lacks teaching to wash the semiconductor wafer, which is drenched with an aqueous abrasive slurry, with an aqueous washing solution, and to rinse the washed semiconductor wafer.

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4. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

## **Contact Information**

5. Any inquiry concerning this communication from the Examiner should be directed to Calvin Lee at (571) 272-1896 on Mondays thru Thursdays 6:30-4:30PM. If attempts to reach the examiner by telephone are unsuccessful, Art Unit 2818's Supervisory Patent Examiner David Nelms can be reached at (571) 272-1787. The fax phone number for the organization (where this application is assigned to) is (571) 273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system at http://pair-direct.uspto.gov. Should you have questions on access to the PAIR system, contact the Electronic Business Center at (866) 217-9197.

CL David Nelms

Supervisory Patent Examiner Technology Center 2800

Dated: September 7, 2005